

JMTL84K
Features

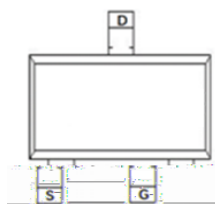
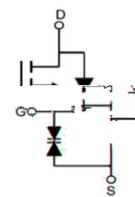
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

- Load Switch
- PWM Application
- Power Management

Product Summary

Parameters	Value	Unit
V_{DSS}	-50	V
$V_{GS(th_Typ)}$	-1.4	V
$I_D(@V_{GS}=10V)$	-0.44	A
$R_{DS(ON_Typ)}(@V_{GS}=-10V)$	2.0	Ω
$R_{DS(ON_Typ)}(@V_{GS}=-4.5V)$	2.1	Ω


SOT-23 Top View

Pin Assignment

Schematic Diagram
Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMTL84K	B84K	3	Tape&Reel	SOT-23	3000	120000

Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	-50	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	A
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽²⁾	131	

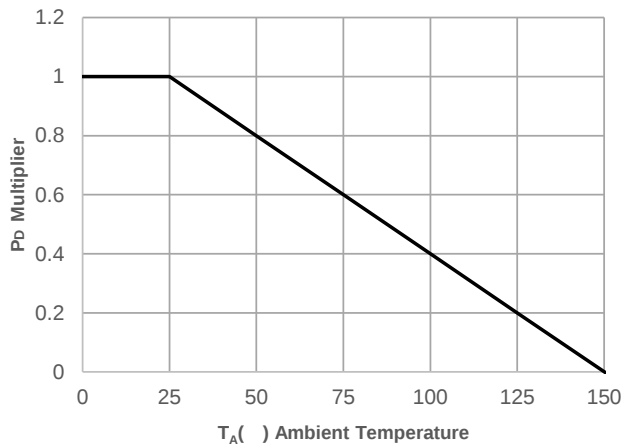
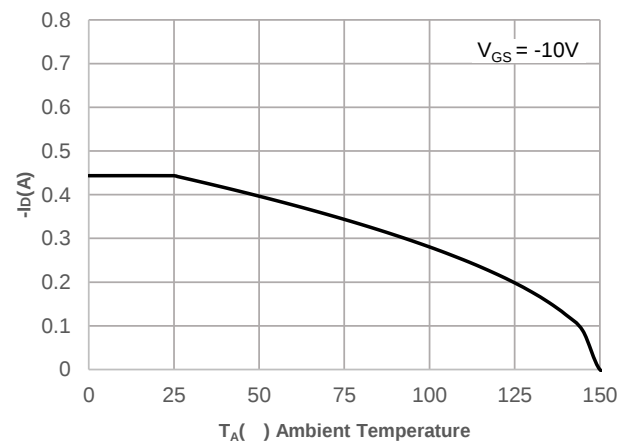
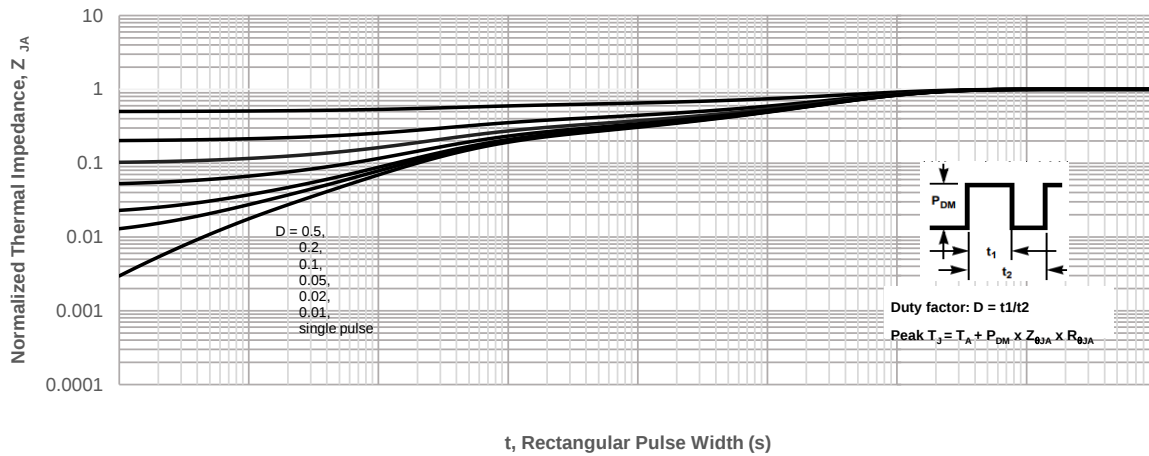
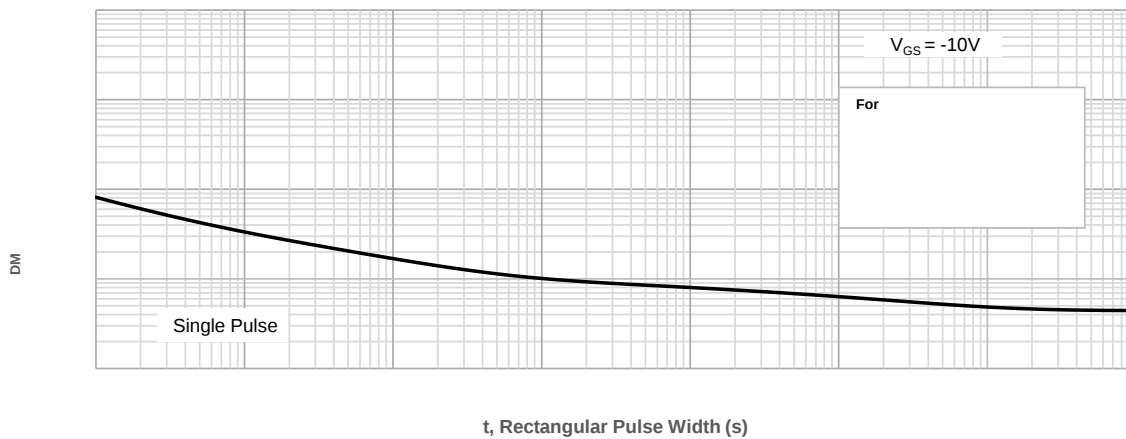


**Electrical Characteristics** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = -250μA, V _{GS} = 0V	-50	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -50V, V _{GS} = 0V	-	-	-1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±10	μA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.4	-1.9	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽³⁾	V _{GS} = -10V, I _D = -0.13A	-	2.0	2.6	Ω
		V _{GS} = -4.5V, I _D = -0.1A	-	2.1	3.6	Ω
Dynamic Characteristics						
R _g	Gate Resistance	f = 1MHz	-	154	-	Ω
C _{iSS}	Input Capacitance	V _{GS} = 0V, V _{DS} = -25V, f = 1MHz	-	55	82	pF
C _{oss}	Output Capacitance		-	13	-	pF
C _{rSS}	Reverse Transfer Capacitance		-	6.7	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to -10V V _{DS} = -25V, I _D = -2A	-	1.7	-	nC
Q _{gs}	Gate Source Charge		-	0.5	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	0.3	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = -10V, V _{DD} = -25V I _D = -2A, R _{GEN} = 3Ω	-	2	-	ns
t _r	Turn-On Rise Time		-	2	-	ns
t _{d(off)}	Turn-Off DelayTime		-	16	-	ns
t _f	Turn-Off Fall Time		-	12	-	ns
Body Diode Characteristics						
I _S	Maximum Continuous Body Diode Forward Current		-	-	-0.4	A
I _{SM}	Maximum Pulsed Body Diode Forward Current		-	-	-1.8	A
V _{SD}	Body Diode Forward Voltage	V _{GS} = 0V, I _S = -0.13A	-		-1.2	V
trr	Body Diode Reverse Recovery Time	I _F = -2A, di/dt = 100A/us	-	22	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	16	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. $R_{\theta JA}$ is measured with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square pad layout.
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Typical Performance Characteristics

Figure 1: Power De-rating

Figure 2: Current De-rating

Figure 3: Normalized Maximum Transient Thermal Impedance

Figure 4: Peak Current Capacity


Typical Performance Characteristics

Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

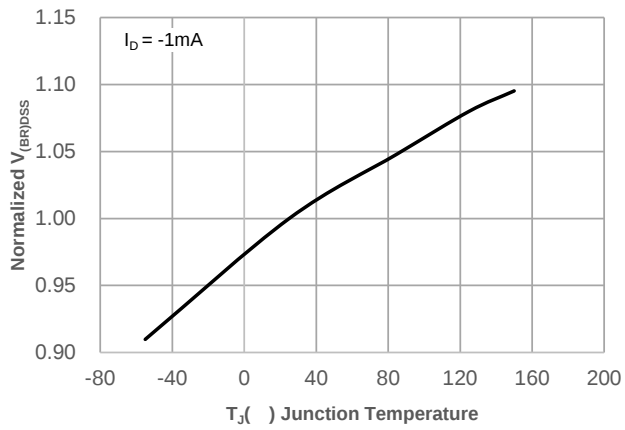
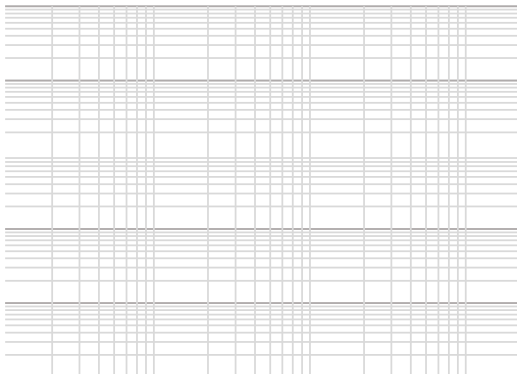
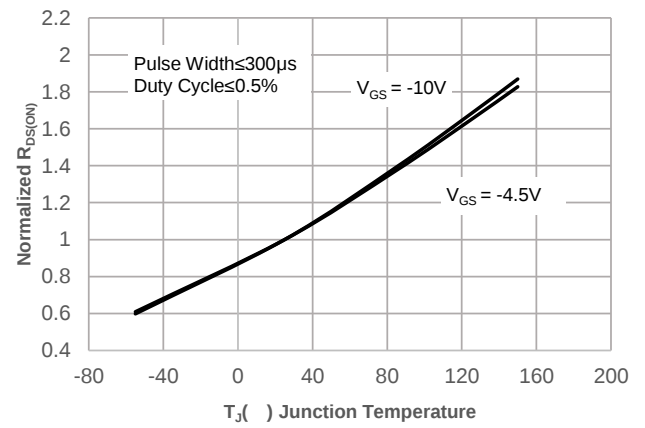


Figure 12: Normalized on Resistance vs. Junction Temperature



Test Circuit

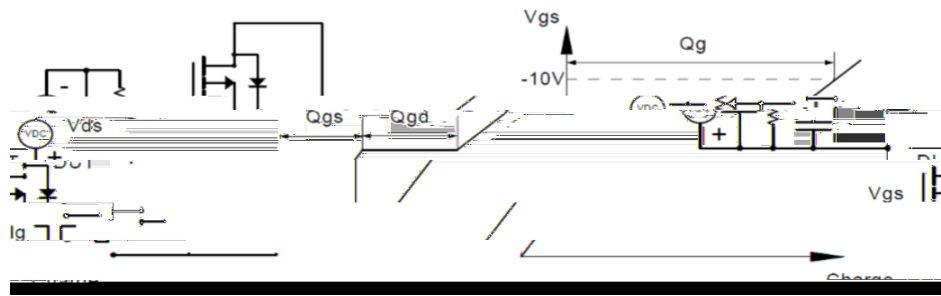


Figure 1: Gate Charge Test Circuit & Waveform

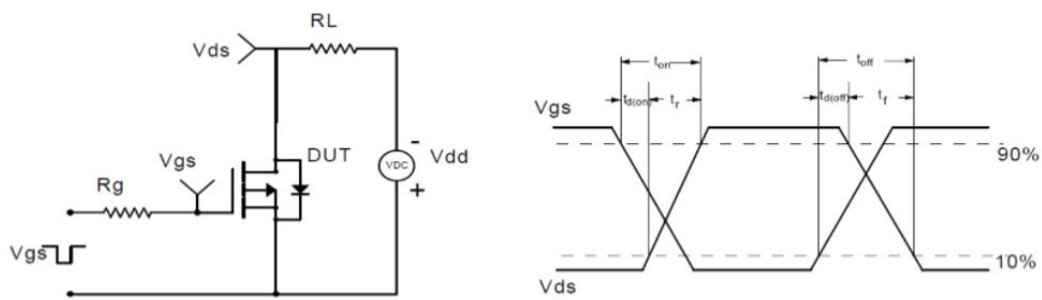


Figure 2: Resistive Switching Test Circuit & Waveform

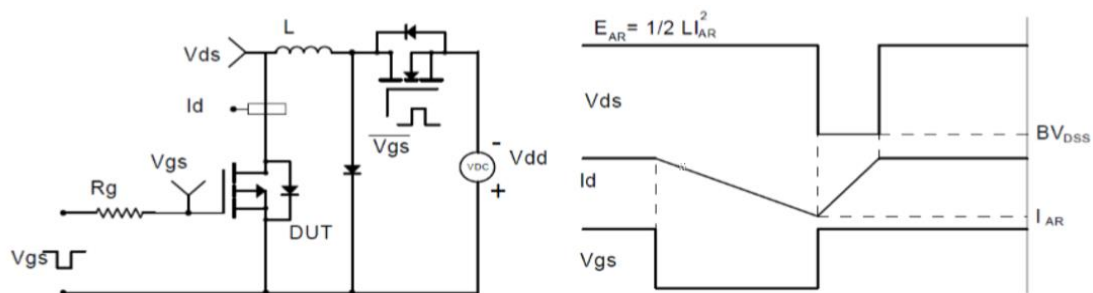


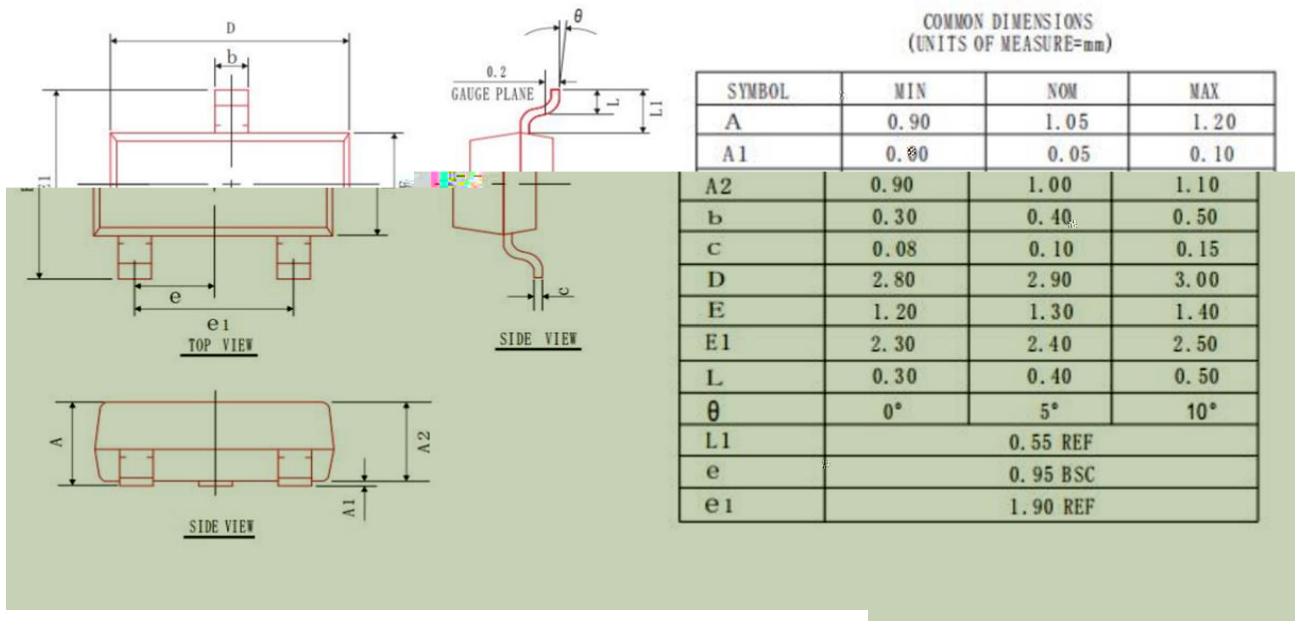
Figure 3: Unclamped Inductive Switching Test Circuit & Waveform



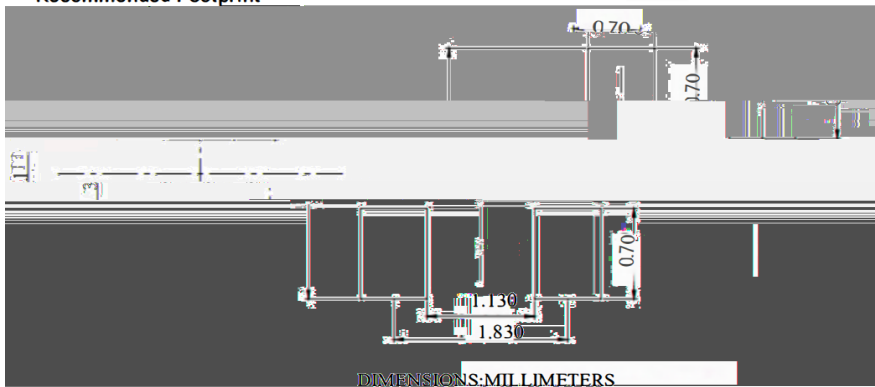
Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOT-23)

Package Outline



Recommended Footprint



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